

A-8753W PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Gerald J. BANKS

Appln. No.: 10/742,890

Group Art Unit: 2824

Filed: December 23, 2003

Examiner: H. Nguyen

For: MEMORY APPARATUS INCLUDING PROGRAMMABLE NON-VOLATILE

MULTI-BIT MEMORY CELL, AND APPARATUS AND METHOD FOR

DEMARCATING MEMORY STATES OF CELL

Allowed: May 18, 2004

Confirmation No.: 7102

REQUEST FOR ACKNOWLEDGEMENT OF INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Attn: Mail Stop Issue Fee

Sir:

An Information Disclosure Statement was filed on May 17, 2004, prior to the allowance of the subject application. A copy of the Information Disclosure Statement and the date-stamped postcard receipt are attached.

Applicant respectfully requests that the Examiner confirm consideration of the Information Disclosure Statement by returning an endorsed copy of the Form PTO-1449.

Respectfully submitted,

y: / /////

Mitchell W. Shapiro

Reg. No. 31,568

MWS:sjk

Miles & Stockbridge P.C. 1751 Pinnacle Drive Suite 500 McLean, Virginia 22102-3833 (703) 903-9000

June 1, 2004



it: Gerald J. BANKS

T3055-907736US02 A-8753W

Filed On:

Vo.: 10/742,890

December 23, 2003

For:

MEMORY APPARATUS INCLUDING PROGRAMMABLE NON-VOLATILE MULTI-BIT MEMORY CELL, AND APPARATUS AND METHOD FOR

DEMARCATING MEMORY STATES OF CELL

Attached: Information Disclosure Statement w/ Form PTO-1449.

RECEIVED IN U.S. PATENT AND TRADEMARK OFFICE ON:



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Gerald J. BANKS

Appln. No.: 10/742,890 Group Art Unit: 2818

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DEMARCATING MEMORY STATES OF CELL

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents Washington, D.C. 20231

Sir:

Applicant wishes to make of record the documents cited in predecessor Application Nos. 10/188,835 filed July 5, 2002, 09/893,545 filed June 29, 2001, 09/733,937 filed December 12, 2000, 09/493,139 filed January 28, 2000, 09/411,315 filed October 4, 1999, 08/975,919 filed November 21, 1997, and 08/410,200 filed February 27, 1995, whether cited by Applicant or by the Patent Office. The documents are listed on the attached Form-1449 and include all citations through AT on sheet 27 of the List. The

remaining document on sheet 27 is the patent which issued on parent Application No. 10/188,835.

The Commissioner is hereby authorized to charge to Deposit Account No. 50-1165 any fees that may be required by this paper and to credit any overpayment to that Account.

Respectfully submitted,

By

Mitchell W. Shapir

Reg. No. 31,568

MWS:sjk

Miles & Stockbridge P.C. 1751 Pinnacle Drive Suite 500 McLean, Virginia 22102-3833 (703) 903-9000

May 17, 2004

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	AA	5,200,920	04/06/93	Norma	m et al.		365	185	
	AB	Re 32,401	04/14/87	Belis	tein, Jr.	et al	365	182	
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Examiner Initial		Document Number	Date	Name	Class	Sub- class	Filing Date
	AA	4,417,325	11/22/83	Harari	365	185	
	АВ	4,448,400	5/15/84	Harari	365	185	
	AC	4,612,629	9/16/86	Harari	365	185	
	AD	5,043,940	8/27/91	Harari	365	168	
	AE	5,163,021	11/10/92	Mehrotra et al.	365	185	
	AF	5,168,465	12/1/92	Harari	257	320	
	AG	5,198,380	3/30/93	Harari	437	43	
	АН	5,200,959	4/6/93	Gross et al.	371	21.6	
	ΑI	5,268,318	12/7/93	Harari	437	43	
	AJ	5,268,319	12/7/93	Harari	437	43	
	AK	5,268,870	12/7/93	Harari	365	218	
	AL	5,272,669	12/21/93	Samachisa et al.	365	185	
	AM	5,293,560	3/8/94	Harari	365	185	
	AN	5,313,421	5/17/94	Guterman et al.	365	185	
	AO	5,422,842	6/6/95	Cernea et al.	365	185	
	AP	5,428,621	6/27/95	Mehrotra et al.	371	21.4	
	AQ	5,430,859	7/4/95	Norman et al.	395	425	
	AR	5,434,825	7/18/95	Harari	365	185	
	AS	5,495,442	2/27/96	Cernea et al.	365	185.03	
	AT	5,544,118	8/6/96	Harari	365	218	
	AU	5,554,553	9/10/96	Harari	437	43	
	AV	5,568,439	10/22/96	Harari	365	218	
	AW	5,583,812	12/10/96	Harari	365	185.33	
	AX	5,642,312	6/24/97	Harari	365	185.33	
	AY	5,657,332	8/12/97	Auclair et al.	371	40.11	
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	ва	5,712,180	1/27/98	Guterman et al.	. 4	437	43	
	вв	5,712,819	1/27/98	Harari	3	365	185.29	
	вс	5,776,810	7/7/98	Guterman et al.	4	138	258	
	ВD	5,806,070	9/8/98	Norman et al.	7	711	103	
-	BE	4,661,929	4/285/87	Aoki et al.	3	365	189	
	BF	4,701,884	10/20/87	Aoki et al.	3	365	189	·
	ВG	4,709,350	11/24/87	Nakagome et al.	3	365	45	
	вн	5,014,242	5/7/91	Akimoto et al.	3	365	63	
	ві	5,299,165	3/29/94	Kimura et al.	3	365	210	
	вЈ	5,307,304	4/26/94	Saito et al.	3	365	145	
,	BK	5,802,553	9/1/98	Robinson et al.	7	11	103	-
	BL	5,801,991	9/1/98	Keeney et al.	3	65	185.23	
	вм	5,796,667	8/18/98	Sweha et al.	3	65	207	
	BN	5,781,472	7/14/98	Sweha et al.	3	65	185.11	
	во	5,754,566	5/19/98	Christopherson et	al. 3	71	40.18	
	BP	5,748,546	5/5/98	Bauer et al.	3	65	210	
	BQ	5,671,388	9/23/97	Hasbun	3	95	430	
•	BR	5,574,879	11/12/96	Wells et al.	3	95	427	
	BS	5,566,125	10/15/96	Fazio et al.	3	65	45	
	вт	5,563,828	10/8/96	Hasbun et al.	3	65	185.33	
	BU	5,553,020	9/3/96	Keeney et al.	3	65	185.19	
	вv	5,546,042	8/13/96	Tedrow et al.	3	27	538	
	BW	5,497,354	3/5/96	Sweha et al.	3	65	230.06	
	вх	5,487,033,	1/23/96	Keeney et al.	3	65	185.19	
	вч	5,438,546	8/1/95	Ishac et al.	3	65	200	

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December 23, 2003

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	AA	4,192,014	03/04/80	Craycraft	365	104			
	AB	4,357,685	11/02/82	Daniele et al.	365	189			
	AC	4,964,079	10/16/90	Devin	365	168			
	AD	5,172,338	12/15/92	Mehrotra et al.	365	185			
	AE	5,262,984	11/16/93	Noguchi et al.	365	185			
	AF	3,801,965	04/02/74	Keller et al.	340	173R			
	AG	4,004,159	01/18/77	Rai et al.	307	238			
	AH	4,054,864	10/18/77	Audaire et al.	340	173R			
	ΑI	4,090,258	05/16/78	Cricchi	,365	184			
	АJ	4,122,541	10/24/78	Uchida	365	154			
	AK	4,139,910	02/13/79	Anantha et al.	365	183			
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	AL	W082/02276	07/08/82	WIPO					
	AM	W082/02976	09/02/82	WIPO					
	AN	WO90/01984	03/08/90	WIPO					
	AO	2 630 574	10/27/89	France			Abstract		
	AP	0 390 404	10/03/90	Europe					
	AQ	0 725 403	08/07/96	EPO					
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	AR	IEEE Intern	M. Bauer et al., A Multilevel-Cell 32Mb Flash Memory, 1995 IEEE International Solid-State Circuits Conference, Session 7, Paper TA7.7.						
	AS	Computer, 1	981 IEEE 3	l., <i>The Interface Pr</i> International Solid- 1981, at 116-117.			41		

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	AA*	4,149,270	04/10/79	Cricchi et al.	365	222	
	AB*	4,181,980	01/01/80	McCoy	365	45	
	AC*	4,272,830	06/09/81	Moench	365	45	
	AD*	4,287,570	09/01/81	Stark	365	104	
	AE*	4,300,210	11/10/81	Chakravarti et al.	365	45	
	AF*	4,306,300	12/15/81	Terman et al.	365	45	
	AG*	4,327,424	04/27/82	Wu	365	104	
-	AH*	4,388,702	06/14/83	Sheppard	365	104	
	AI*	4,415,992	11/15/83	Adlhoch	365	94	
	AJ*	4,449,203	05/15/84	Adlhoch	365	104	
	AK*	4,462,088	07/24/84	Giuliani et al.	365	105	
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Date Considered

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	Applicant Gerald J. BANKS	
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	AA^	4,495,602	01/22/85	Sheppard		365	.104	·
	AB^	4,503,518	03/05/85	Iwahashi		365	104	·
	AC^	4,558,241	12/10/85	Suzuki e	t al.	307	530	
	AD^	4,578,777	03/25/86	Fang et a	al.	365	184	
	AE^	4,586,163	04/29/86	Koike		365	104	
	AF^	4,627,027	12/02/86	Rai et al		365	45	
	AG^	4,653,023	03/24/87	Suzuki et	al.	365	104	
	AH^	4,661,929	04/28/87	Aoki et a	1.	365	189	
	AI^	4,709,350	11/24/87	Nakagome	et al.	365	45	
	AJ^	4,733,394	03/22/88	Giebel		371	21	
	AK^	4,771,404	09/13/88	Mano et a	1.	365	189	
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	R.S. Withers et al., Nonvolatile Analog Memory in MNOS Capacitors, IEEE Electron Device Letters, Vol. EDL-1, No. 3, March 1980, at 42-45.							
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Date Considered

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	Gerald J. BANKS	
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	AA#	4,799,195	01/17/89	Iwahashi e	et al.	365	185	
	AB#	4,847,808	07/11/89	Kobatake		364	104	
	AC#	4,853,892	08/01/89	Hori		365	49	
	AD#	4,890,259	12/26/89	Simko		365	45	
	AE#	4,914,631	04/03/90	Johnson et	al.	365	189.11	
	AF#	4,989,179	01/29/91	Simko		365	45	
	AG#	5,021,999	06/04/91	Kohda et a	1.	365	168	
	жн#	5,043,940	08/27/91	Harari		365	168	
	AI#	5,095,344	03/10/92	Harari		357	23.5	
	AJ#	5,163,021	11/10/92	Mehrotra e	t al.	365	185	
·	AK#	5,258,958	11/02/93	Iwahashi e	t al.	365	210	
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Date Considered

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	AA'	5,268,870	12/07/93	Harari		365	218	
	AB'	5,293,560	03/08/94	Harari		365	185	
	AC'	5,321,655	06/14/94	Iwahashi	et al.	365	200	
· 	AD'	5,351,210	09/27/94	Saito		365	189.01	
	AE'	5,422,845	06/06/95	Ong		365	185	
	AF'	5,432,735	07/11/95	Parks et	al.	365	168	
	AG'	5,434,825	07/18/95	Harari		365	185	
	AH'	5,440,505	08/08/95	Fazio et	al.	365	45	
	AI'	5,444,656	08/22/95	Bauer et	al.	365	189.01	
	AJ'	5,450,363	09/12/95	Christophe	rson et al.	365	205	
	AK'	5,457,650		Sugiura (365	184	
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	AA~	5,469,384	11/21/95	Lacey	365	185.13	
	AB~	5,475,693	12/12/95	Christopherson et al.	371	10.2	
	AC~	5,485,422	01/16/96	Bauer et al.	365	168	
	AD~	5,497,119	03/05/96	Tedrow et al.	327	540	·
	AE~	5,506,813	04/09/96	Mochizuki et al.	365	230.03	
	AF~	5,508,958	04/16/96	Fazio et al.	365	185.19	
	AG~	5,515,317	05/07/96	Wells et al.	395	427	
	AH~	5,523,972	06/04/96	Rashid et al.	365	185.22	
	AI~	5,539,690	07/23/96	Talreja et al.	365	185.22	
	AJ~	5,541,886	07/30/96	Hasbun	365	230.01	
	AK~	5,544,118	08/06/96	Harari	365	218	
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